

ABSTRACT OF THE DISCLOSURE

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METHOD FOR PRODUCING CONTACT STRUCTURE

A production method for forming contact structures on a planar surface of a substrate. The production method includes the steps of: (a) forming a sacrificial layer on a surface of a silicon substrate, (b) forming an conductive layer made of electric conductive material on the sacrificial layer, (c) forming a photoresist layer on the conductive layer, (d) aligning a photo mask over the photoresist layer and exposing the photoresist layer with ultraviolet light through the photo mask where the photo mask including an image of the contact structures, (e) developing the image on the photoresist layer which has openings on the surface of the photoresist layer, (f) forming the contact structures made of electric conductive material in the openings by an electroplating process, (g) stripping the photoresist layer, (h) removing the sacrificial layer by a first etching process so that the contact structures are separated from the silicon substrate, and (i) removing the conductive layer from the contact structure by a second etching process.

FIG. 2A



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